

# BCR08AS-12A

# Triac

Low Power Use

REJ03G0292-0300 Rev.3.00 Nov 30, 2007

### **Features**

 $I_{T (RMS)} : 0.8 A$  $V_{DRM}$ : 600 V

I<sub>FGTI</sub>, I<sub>RGTI</sub>, I<sub>RGT III</sub>: 5 mA

 $I_{FGT}$ : 10 mA

Non-Insulated Type

Planar Passivation Type

Completed Pb Free

### **Outline**

RENESAS Package code: PLZZ0004CA-A (Package name: UPAK)



RENESAS Package code: PLZZ0004CB-A (Package name: SOT-89)





T<sub>1</sub> Terminal
 T<sub>2</sub> Terminal

3. Gate Terminal 4. T<sub>2</sub> Terminal

# **Applications**

Hybrid IC, solid state relay, electric fan, washing machine, and other general purpose control applications

## **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	
raiailletei	Symbol	12 (Mark BF)		
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	600	V	
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	720	V	

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	0.8	А	Commercial frequency, sine full wave 360° conduction, Ta = 40°C <sup>Note3</sup>
Surge on-state current	I <sub>TSM</sub>	8	А	60Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	0.26	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	1	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.1	W	
Peak gate voltage	$V_{GM}$	10	V	
Peak gate current	$I_{GM}$	1	Α	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
Mass	_	50	mg	Typical value

Notes: 1. Gate open.

# **Electrical Characteristics**

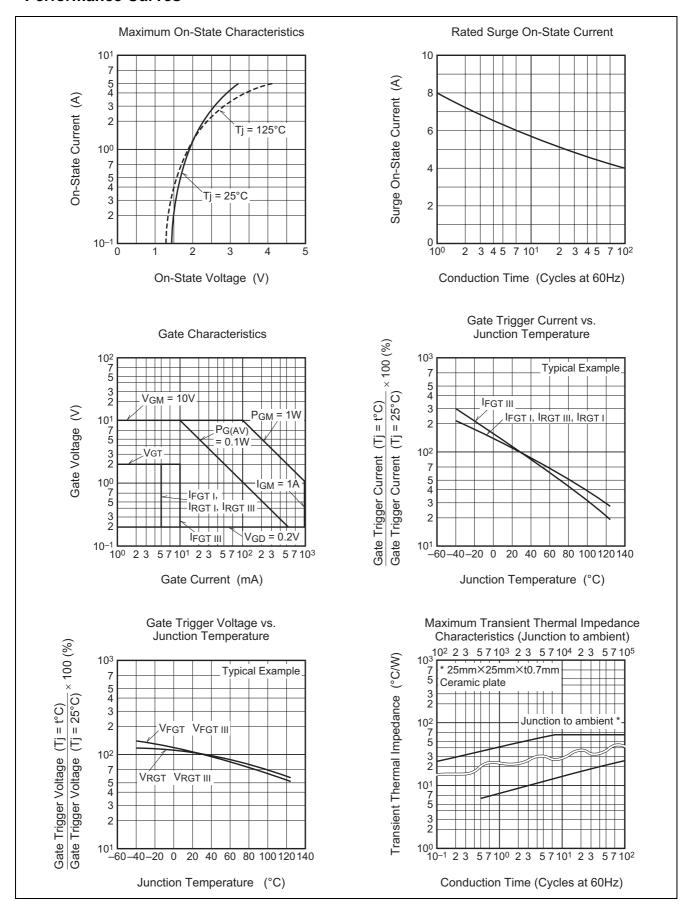
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>	_	_	2.0	mA	Tj = 125°C, V <sub>DRM</sub> applied
On-state voltage		$V_{TM}$		_	2.0	V	Tc = 25°C, I <sub>TM</sub> = 1.2 A, Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGTI}$	_	_	2.0	V	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	$V_{RGTI}$	_	_	2.0	V	$R_G = 330 \Omega$
	III	$V_{RGTIII}$	_	_	2.0	V	
	IV	$V_{FGTIII}$	_	_	2.0	V	
Gate trigger current <sup>Note2</sup>	I	$I_{\text{FGTI}}$	_	_	5	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	$I_{RGTI}$		_	5	mA	$R_G = 330 \Omega$
	III	$I_{RGTIII}$		_	5	mA	
	IV	I <sub>FGTIII</sub>	_	_	10	mA	
Gate non-trigger voltage		$V_{GD}$	0.1	_	_	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-a)</sub>	_	_	65	°C/W	Junction to ambient <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>		(dv/dt)c	0.5	_	_	V/μs	Tj = 125°C

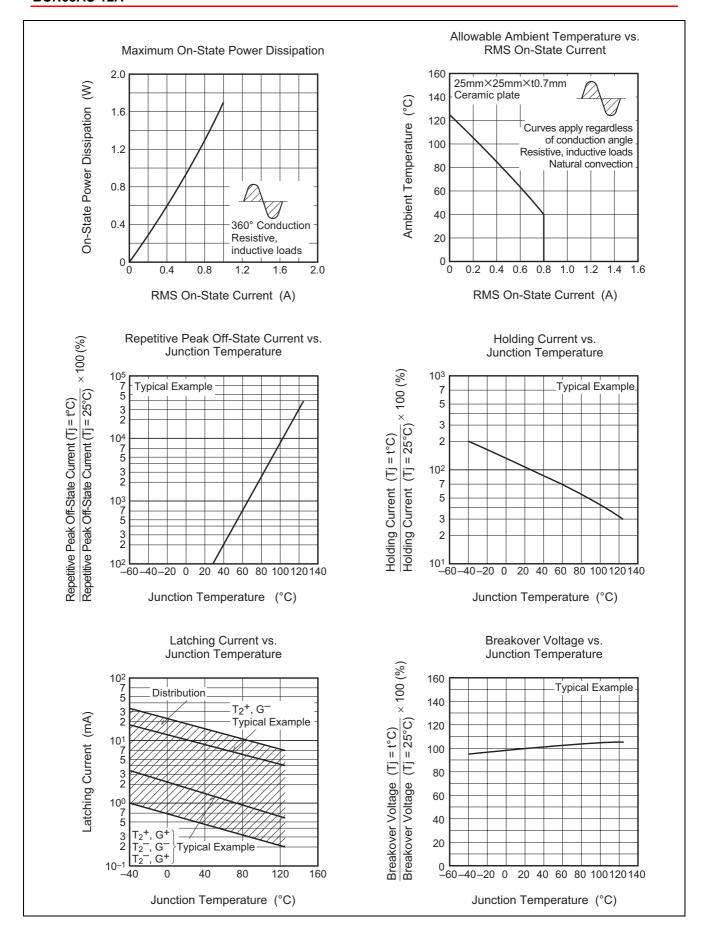
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

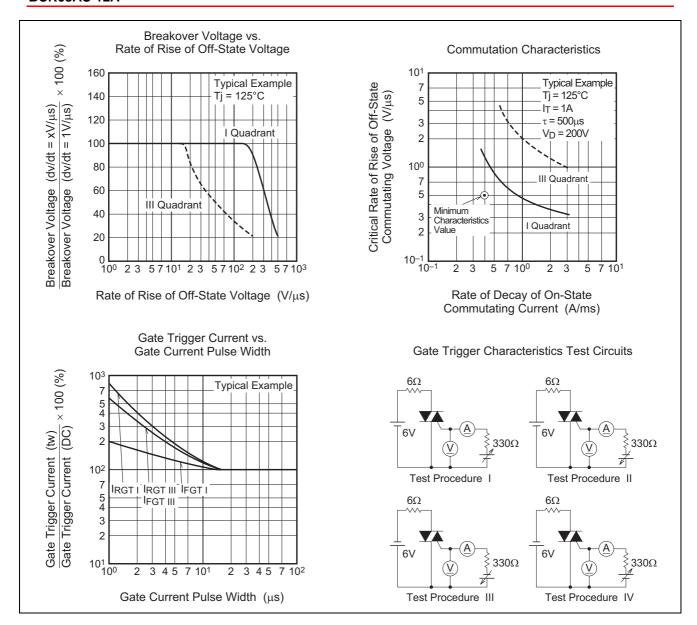
- 3. Soldering with ceramic plate (25 mm  $\times$  25 mm  $\times$  t0.7 mm).
- 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature Tj = 125°C	Supply Voltage  → Time
2. Rate of decay of on-state commutating current (di/dt)c = - 0.4 A/ms	Main Current (di/dt)c - Time
3. Peak off-state voltage V <sub>D</sub> = 400 V	Main Voltage Time

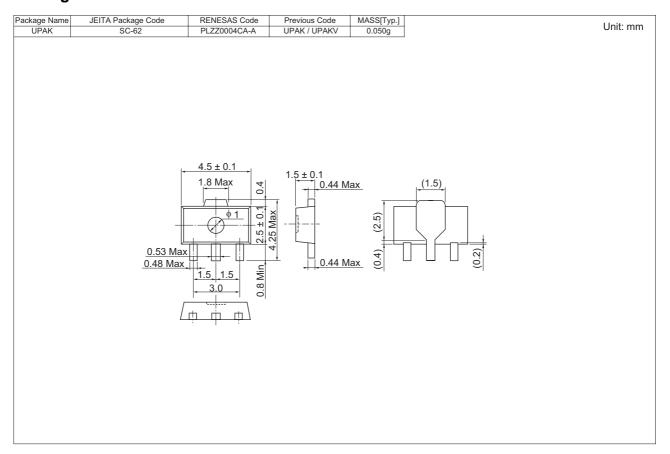
### **Performance Curves**

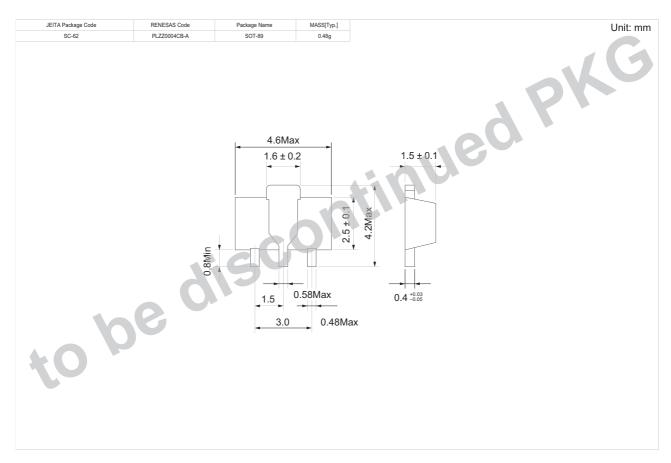






## **Package Dimensions**





# **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	4000	Type name -T +Direction (1 or 2)+4	BCR08AS-12A-T14

Note: Please confirm the specification about the shipping in detail.

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